

S/N 08/903,486

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Serial No.: 08/903,486

Filed: July 29, 1997

Title: SILICON CARBIDE TRANSISTOR



Examiner: W. Mintel

Group Art Unit: 2811

Docket: 303.326US1

PATENT

AMENDMENT AND RESPONSE

RECEIVED
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Commissioner for Patents
Washington, D.C. 20231

The applicant has reviewed the Office Action mailed June 6, 2000. Please amend the application as follows:

IN THE CLAIMS

Please cancel claims 6, 7, 23, 30, 36, 49 and 54 and amend the claims as follows:

Subj D1

1. [Twice Amended] A transistor comprising:
a source region, a drain region, and a channel region between the source and drain regions in a semiconductor surface layer formed on an underlying insulating portion, and an electrically interconnected gate formed of a silicon carbide [material] compound $Si_{1-x}C_x$, wherein x is less than 0.5, the gate being connected to receive an input signal.

Subj D2

11. [Twice Amended] An integrated circuit device comprising:
a substrate;
a p-channel transistor formed in a first portion of the substrate, the p-channel transistor including a source region, a drain region, a channel region between the source and drain regions, and an electrically interconnected silicon carbide gate over the channel region and separated therefrom by an insulating layer, the gate of the p-channel transistor comprising a silicon carbide compound $Si_{1-x}C_x$, wherein x is less than 0.5, and being connected to receive a first input signal;
and
an n-channel transistor formed in a second portion of the substrate, the n-channel transistor including a source region, a drain region, a channel region between the source and drain regions, and an electrically interconnected silicon carbide gate over the channel region and separated therefrom by an insulating layer, the gate of the n-channel transistor comprising a